

MCR12D, MCR12M, MCR12N

Preferred Device

Silicon Controlled Rectifiers

Reverse Blocking Thyristors

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave silicon gate-controlled devices are needed.

Features

- Blocking Voltage to 800 Volts
- On-State Current Rating of 12 Amperes RMS at 80°C
- High Surge Current Capability – 100 Amperes
- Rugged, Economical TO-220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- High Immunity to dv/dt – 100 V/μsec Minimum at 125°C
- Pb-Free Packages are Available*

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open)	V _{DRM} , V _{RRM}		V
	MCR12D	400	
	MCR12M	600	
	MCR12N	800	
On-State RMS Current (180° Conduction Angles; T _C = 80°C)	I _{T(RMS)}	12	A
Peak Non-repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T _J = 125°C)	I _{TSM}	100	A
Circuit Fusing Consideration (t = 8.33 ms)	I ² t	41	A ² sec
Forward Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C)	P _{GM}	5.0	W
Forward Average Gate Power (t = 8.3 ms, T _C = 80°C)	P _{G(AV)}	0.5	W
Forward Peak Gate Current (Pulse Width ≤ 1.0 μs, T _C = 80°C)	I _{GM}	2.0	A
Operating Junction Temperature Range	T _J	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

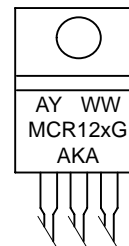
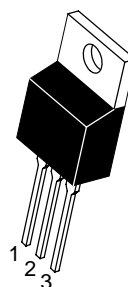


ON Semiconductor®

SCRs
12 AMPERES RMS
400 thru 800 VOLTS



MARKING DIAGRAM



TO-220AB
CASE 221A-09
STYLE 3

- A = Assembly Location
- Y = Year
- WW = Work Week
- x = D, M, or N
- G = Pb-Free Package
- AKA = Diode Polarity

PIN ASSIGNMENT

Pin	Assignment
1	Cathode
2	Anode
3	Gate
4	Anode

ORDERING INFORMATION

Device	Package	Shipping
MCR12D	TO-220AB	50 Units / Rail
MCR12DG	TO-220AB (Pb-Free)	50 Units / Rail
MCR12M	TO-220AB	50 Units / Rail
MCR12MG	TO-220AB (Pb-Free)	50 Units / Rail
MCR12N	TO-220AB	50 Units / Rail
MCR12NG	TO-220AB (Pb-Free)	50 Units / Rail

Preferred devices are recommended choices for future use and best overall value.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.2	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient	$R_{\theta JA}$	62.5	$^{\circ}\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Forward or Reverse Blocking Current ($V_D = \text{Rated } V_{DRM}$ and V_{RRM} ; Gate Open)	I_{DRM} , I_{RRM}	-	-	0.01 2.0	mA
					$T_J = 25^{\circ}\text{C}$
					$T_J = 125^{\circ}\text{C}$

ON CHARACTERISTICS

Peak Forward On-State Voltage (Note 2) ($I_{TM} = 24 \text{ A}$)	V_{TM}	-	-	2.2	V
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}$; $R_L = 100 \Omega$)	I_{GT}	2.0	8.0	20	mA
Holding Current ($V_D = 12 \text{ V}$, Gate Open, Initiating Current = 200 mA)	I_H	4.0	20	40	mA
Latch Current ($V_D = 12 \text{ V}$, $I_G = 20 \text{ mA}$)	I_L	6.0	25	60	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ V}$; $R_L = 100 \Omega$)	V_{GT}	0.5	0.65	1.0	V

DYNAMIC CHARACTERISTICS

Critical Rate of Rise of Off-State Voltage ($V_D = \text{Rated } V_{DRM}$, Exponential Waveform, Gate Open, $T_J = 125^{\circ}\text{C}$)	dv/dt	100	250	-	V/ μs
Repetitive Critical Rate of Rise of On-State Current IPK = 50 A, Pw = 40 μsec , diG/dt = 1 A/ μsec , Igt = 50 mA	di/dt	-	-	50	A/ μs

2. Indicates Pulse Test: Pulse Width $\leq 2.0 \text{ ms}$, Duty Cycle $\leq 2\%$.

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Off State Forward Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Off State Reverse Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Peak On State Voltage
I_H	Holding Current

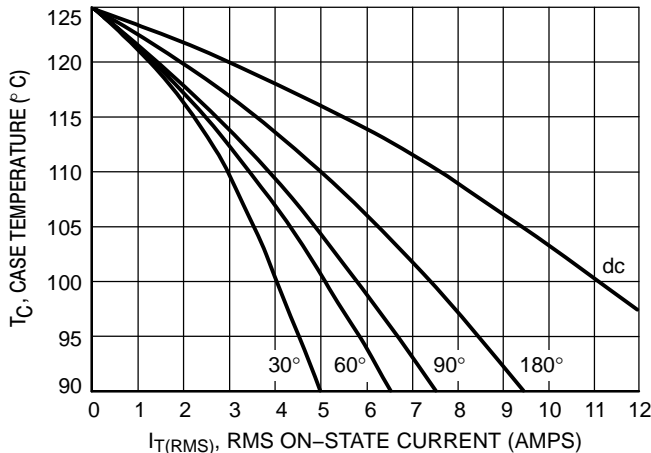
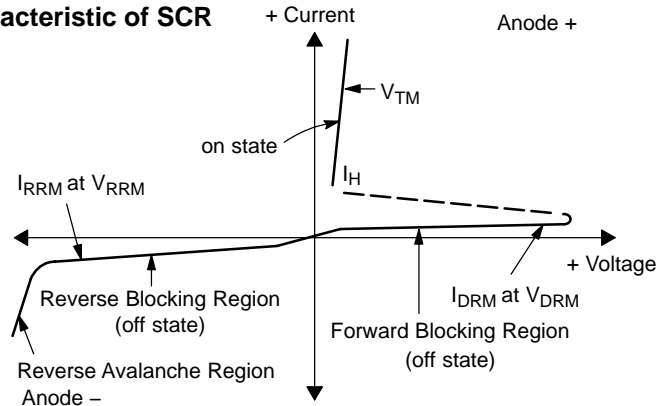


Figure 1. Typical RMS Current Derating

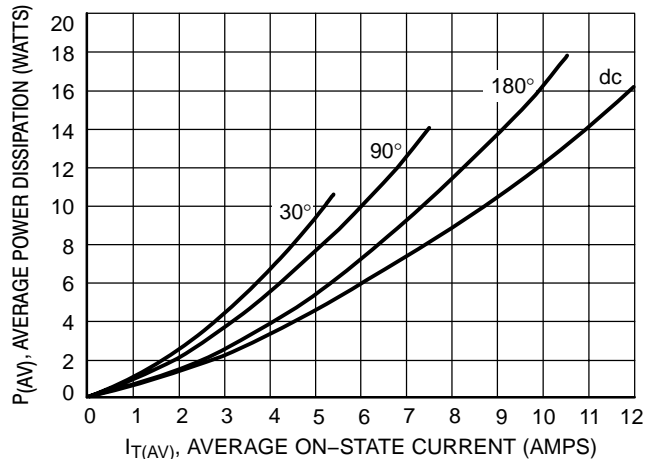
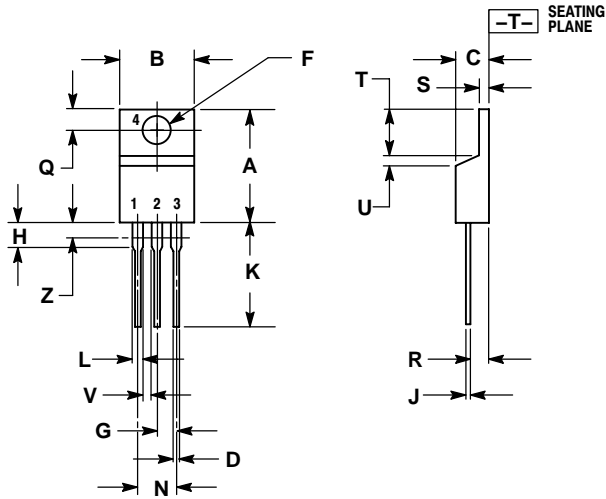


Figure 2. On-State Power Dissipation

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PACKAGE DIMENSIONS

TO-220AB
CASE 221A-09
ISSUE AA



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 3:

- PIN 1. CATHODE
2. ANODE
3. GATE
4. ANODE